

BRCS120N06SRA

Rev.A Apr.-2023

/ Descriptions

N TO-220

N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

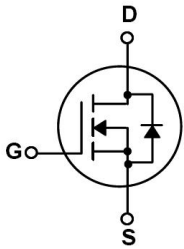
Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching, HF Product.

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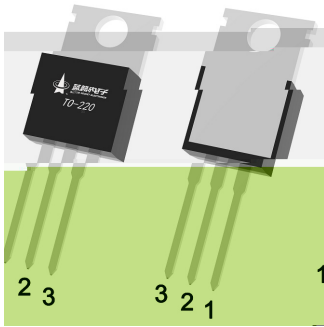
/ Applications

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 D

PIN 3 S

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	60	V
Drain Current	I _D (Tc=25)	60	A
Drain Current - Pulsed	I _{DM}	225	A
Gate-Source Voltage	V _{GS}	±20	V
Avalanche Current	I _{AS}	20	A
Single Pulsed Avalanche Energy	E _{AS}	170	mJ
Power Dissipation	P _D (Tc=25)	96	W
Storage Temperature Range	T _{stg}	-55 150	
Thermal Resistance-Junction to Ambient	t 10s	R _{JA}	15
	Steady-State		62
Thermal Resistance-Junction to Case	Steady-State	R _{JC}	1.3

/ Electrical Characteristics(Ta=25)

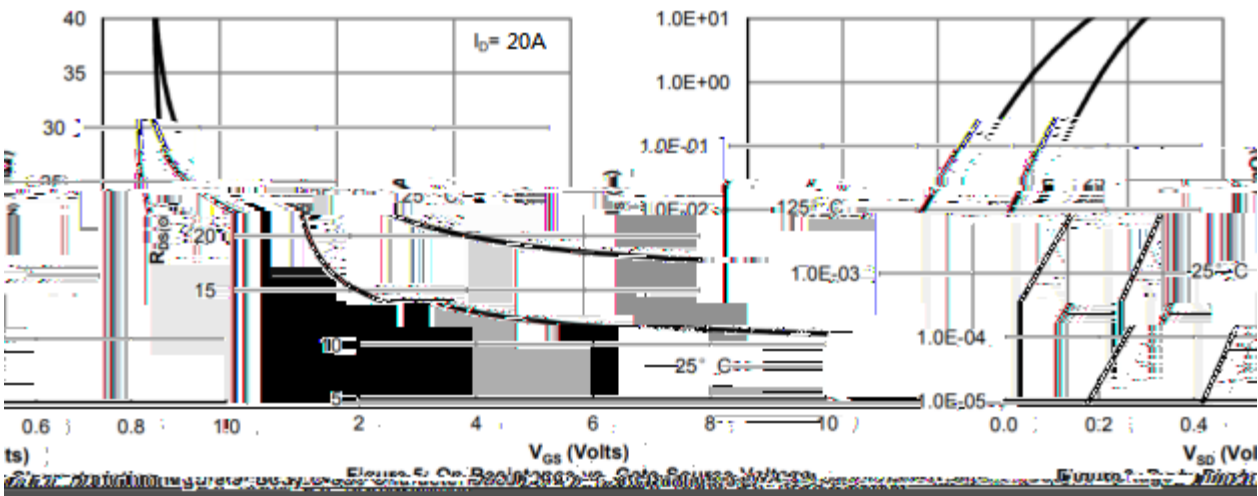
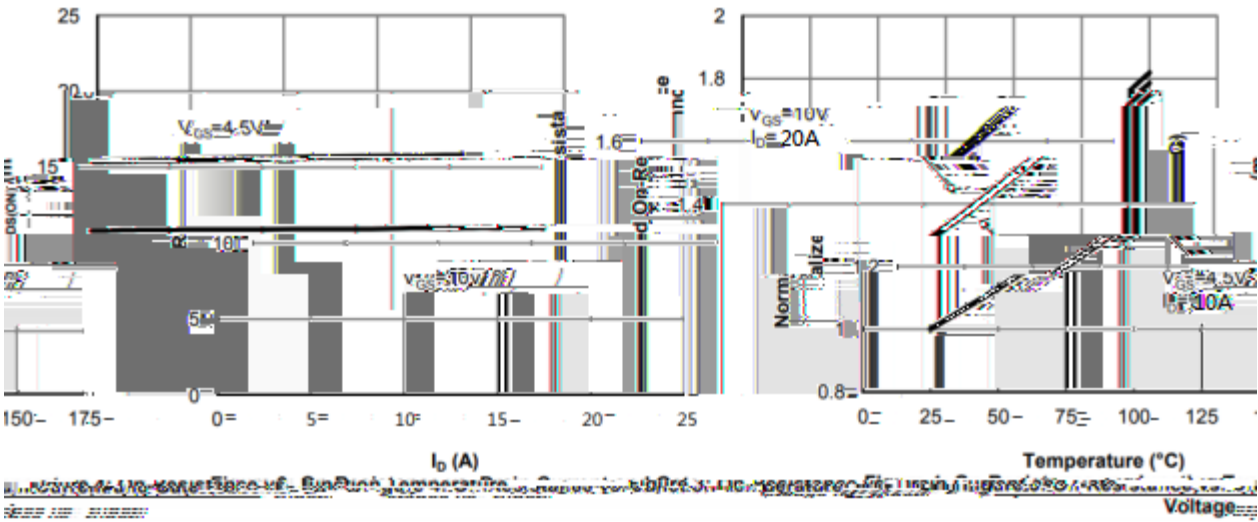
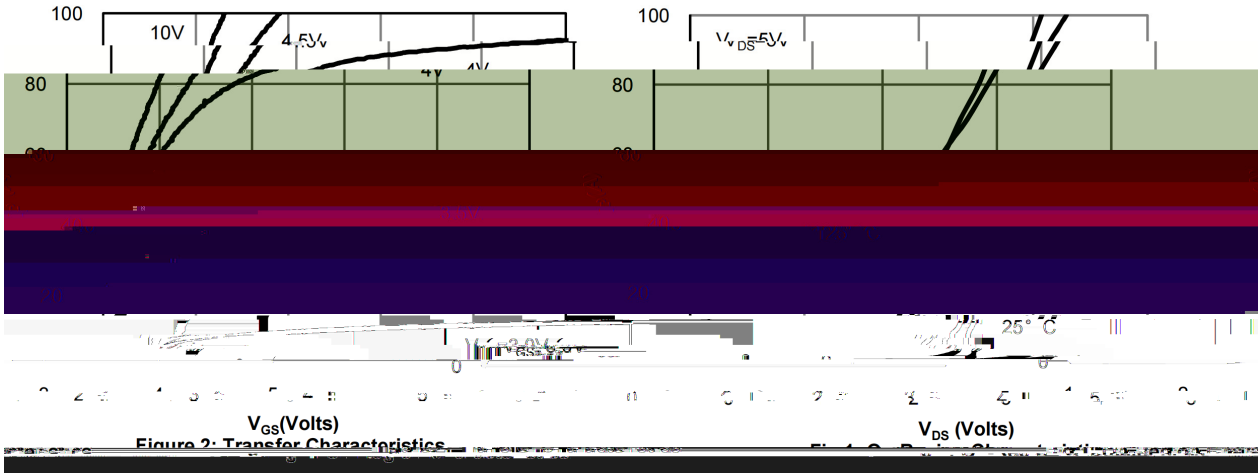
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	63		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V V _{GS} =0V			1.0	μA
		V _{DS} =48V T _C =150			10	
Gate-Body Leakage Current Forward	I _{GSS}	V _{GS} =±20V V _{DS} =0V			±0.1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =250μA	1	1.6	3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V I _D =25A		10.5	15	m
		V _{GS} =4.5V I _D =18A		13.5	20	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V I _S =25A			1.25	V
Gate resistance	R _g	V _{GS} =0V V _{DS} =0V, f=1MHz		1.49		
Input Capacitance	C _{iss}	V _{DS} =25V V _{GS} =0V f=1.0MHz		1010		pF
Output Capacitance	C _{oss}			250		
Reverse Transfer Capacitance	C _{rss}			280		
Total Gate Charge	Q _g (10V)	V _{GS} =10V V _{DS} =30V I _D =20A		22		nC
Total Gate Charge	Q _g (4.5V)			8.7		
Gate Source Charge	Q _{gs}			5.5		
Gate Drain Charge	Q _{gd}			2.6		

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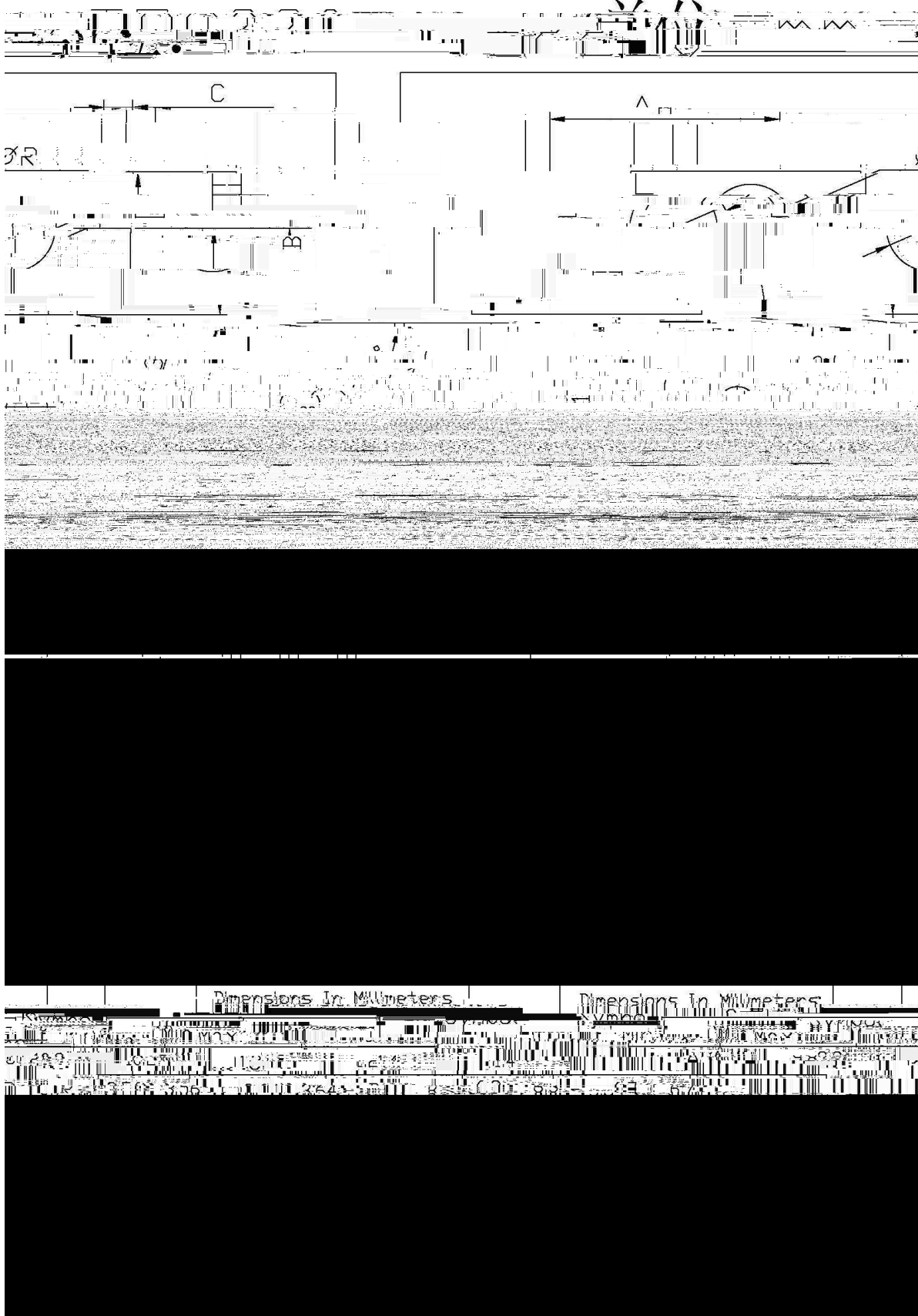
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=30V$ $R_L=1.5$ $R_{GEN}=3$		8.9		ns
Turn-On Rise Time	t_r			3.7		
Turn-Off Delay Time	$t_{d(off)}$			25		
Turn-Off Fall Time	t_f					

/ Electrical Characteristic Curve

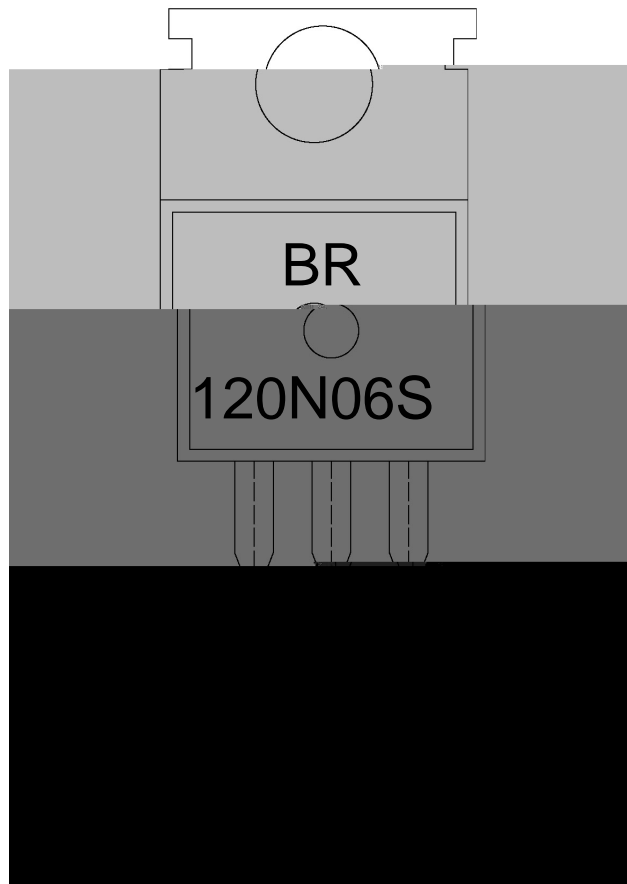


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/ Package Dimensions



/ Marking Instructions



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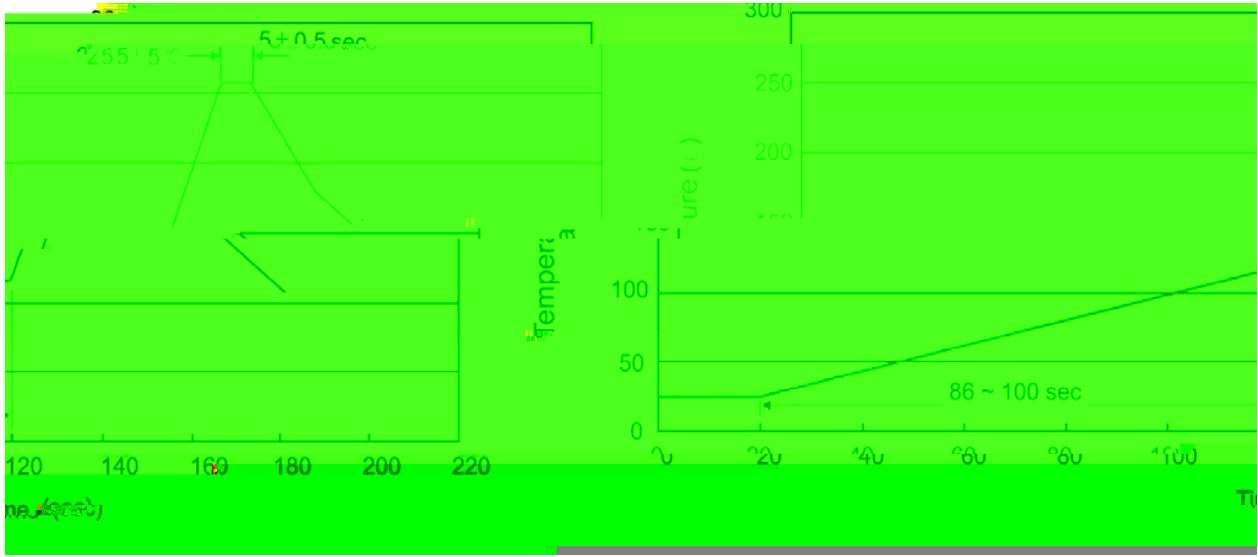
Note:

BR: Company Code

120N06S: Product Type

***: Lot No. Code, code change with Lot No

() / Temperature Profile for Dip Soldering(Pb-Free)



- 1 25 150 60 90sec;
- 2 255±5 5±0.5sec;
- 3 2 10 /sec.

Note:

- 1.Preheating:25~150 , Time:60~90sec.
- 2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

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